Ordering number : ENA0347

SANYO Semiconductors

DATA SHEET

SBT80-10LS — Schottky Barrier Diode (Twin Type · Cathode Common)

100V, 8A Rectifier

Applications

- High frequency rectification (switching regulators, converters, choppers).

Features

- Tj=150°C.
- Low forward voltage (V_F max=0.80V).
- Short reverse recovery time.
- Low switching noise.
- High reliability due to highly reliable planar structure.
- Micaless package facilitating mounting.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		100	V
Nonrepetitive Peak Reverse Surge Voltage	V_{RSM}		105	V
Average Output Current	I_O	50Hz resistive load, Sine wave Tc=81°C	8	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	60	A
Junction Temperature	Tj		−55 to +150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Reverse Voltage	V_R	I_R=1mA, Tj=25°C*	100			V
Forward Voltage	V_F	I_F=3.0A, Tj=25°C*			0.80	V
Reverse Current	I_R	V_R=50V, Tj=25°C*			0.1	mA
Interterminal Capacitance	C	V_R=10V, Tj=25°C*		90		pF
Thermal Resistance	Rth(j-c)	Junction-Case : Smoothed DC			5.0	°C / W

Note) * : Value per element

SANYO Semiconductor Co., Ltd.

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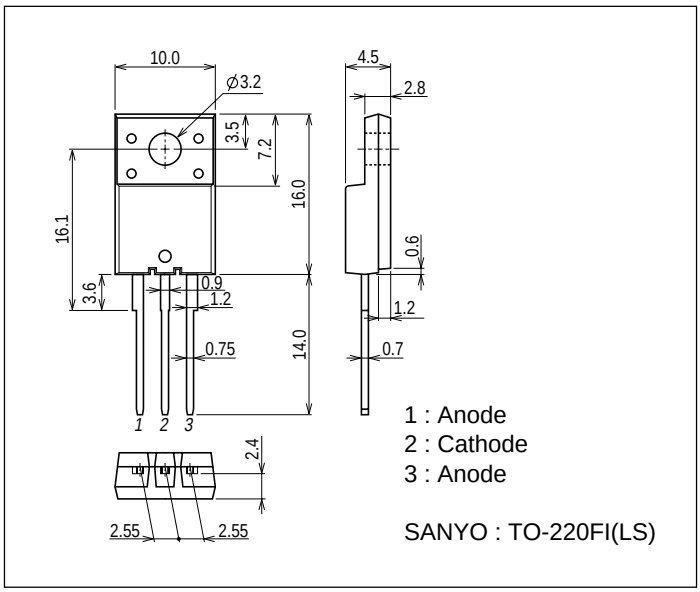
Package Dimensions

unit : mm

7509-001



Electrical Connection